In the claims:

Please amend the claims as follows:

1. (Currently Amended) A structure of a light emitting diode (LED), comprising:

a substrate;

a bragg reflector layer located on said substrate, wherein said bragg reflector comprises:

a first plurality of highly oxidizable semiconductor layers, which when oxidized ~~wherein each of said plurality of oxidizable~~ semiconductor layers is oxidized to form a current insulating layer; and

a second plurality of less oxidizable ~~hardly oxidized~~ semiconductor layers[[,]]; wherein said first plurality of ~~oxidizable semiconductor~~ layers and said second plurality of ~~hardly oxidized semiconductor~~ layers are alternately stacked on each other[[,]] ~~wherein said plurality of oxidizable semiconductor layers are easier to oxidize than said plurality of hardly oxidized semiconductor layers~~ ;

an LED epitaxial structure located on said bragg reflector layer, wherein said LED epitaxial structure comprises an n-type III-V compound semiconductor layer, an illuminating active layer, and a p-type III-V compound semiconductor layer;

a first electrode located on an exposed portion of said n-type III-V compound semiconductor layer; and

a second electrode located on an exposed portion of said p-type III-V compound semiconductor layer.

2. (Cancelled)

3. (Currently Amended) The structure according to claim 1, wherein said second plurality of less oxidizable ~~hardly oxidized semiconductor~~ layers ~~in said bragg reflector layer~~

are AlGaInP layers.

4. (Currently Amended) The structure according to claim 1, wherein said second plurality of less oxidizable ~~hardly oxidized semiconductor~~ layers in said bragg reflector layer are AlInP layers.

5. (Currently Amended) The structure according to claim 1, wherein said second plurality of less oxidizable ~~hardly oxidized semiconductor~~ layers ~~in said bragg reflector layer~~ are low aluminum-~~contained~~ containing AlGaAs layers.

6. (Currently Amended) The structure according to claim 1, wherein said first plurality of oxidizable semiconductor layers ~~in said bragg reflector layer~~ are high aluminum-containing ~~contained~~ AlGaAs layers.

7. (Currently Amended) The structure according to claim 6 [[1]], wherein [[the]] an aluminiferous content of said high aluminum-containing ~~contained~~ AlGaAs layers are between about 80% and about 100%.

8. (Currently Amended) The structure according to claim 6, wherein said current insulating layer is formed by oxidizing each of said high aluminum-containing ~~contained~~ AlGaAs layers at a temperature between about 300 and about 800 degree C.

9 - 16 (Withdrawn)

17. (Currently Amended) A structure of a light emitting diode (LED), comprising:

a substrate;

a bragg reflector layer located on said substrate, wherein said bragg reflector comprises:

a first plurality of highly oxidizable semiconductor layers, which when oxidized ~~wherein each of said plurality of oxidizable semiconductor layers is oxidized to~~ form a current insulating layer, [[and]] said first plurality ~~of oxidizable semiconductor~~ layers

[[are]] being high aluminum-containing ~~contained~~ AlGaAs layers~~, wherein the~~ having an aluminiferous content of ~~said high aluminum contained AlGaAs layers are~~ between about 80% and about 100%; and

a second plurality of less oxidizable ~~hardly oxidized~~ semiconductor layers, wherein said first plurality of oxidizable semiconductor layers and said second plurality of less oxidizable ~~hardly oxidized~~ semiconductor layers are alternately stacked on each other, wherein said firs plurality of less oxidizable semiconductor layers are low aluminum-containing ~~contained~~ AlGaAs layers ;

an LED epitaxial structure located on said bragg reflector layer, wherein said LED epitaxial structure comprises an n-type III-V compound semiconductor layer, an illuminating active layer, and a p-type III-V compound semiconductor layer;

a first electrode located on an exposed portion of said n-type III-V compound semiconductor layer; and

a second electrode located on an exposed portion of said p-type III-V compound semiconductor layer.